# NOR3063, NCR 3063B, NCV3063

# **1.5 A, Step-Up/Down/** Inverting Switching Regulators

The NCP3063 Series is a higher frequency upgrade to the popular MC34063A and MC33063A monolithic DC–DC converters. These devices consist of an internal temperature compensated reference, comparator, a controlled duty cycle oscillator with an active current limit circuit, a driver and a high current output switch. This series was specifically designed to be incorporated in Step–Down, Step–Up and Voltage–Inverting applications with a minimum number of external components.

### Features

- Operation to 40 V Input
- Low Standby Current
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation of 150 kHz
- Precision 1.5% Reference
- New Features: Internal Thermal Shutdown with Hysteresis Cycle-by-Cycle Current Limiting
- Pb–Free Packages are Available

### Applications

- Step–Down, Step–Up and Inverting supply applications
- High Power LED Lighting
- Battery Chargers

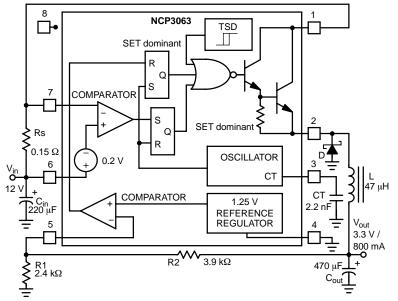
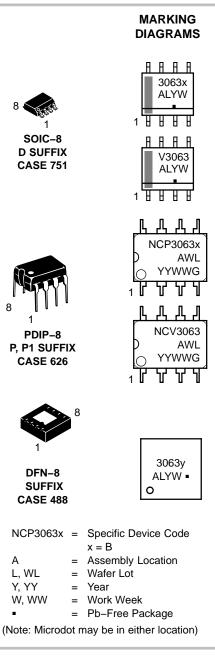


Figure 1. Typical Buck Application Circuit



# **ON Semiconductor®**

http://onsemi.com



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

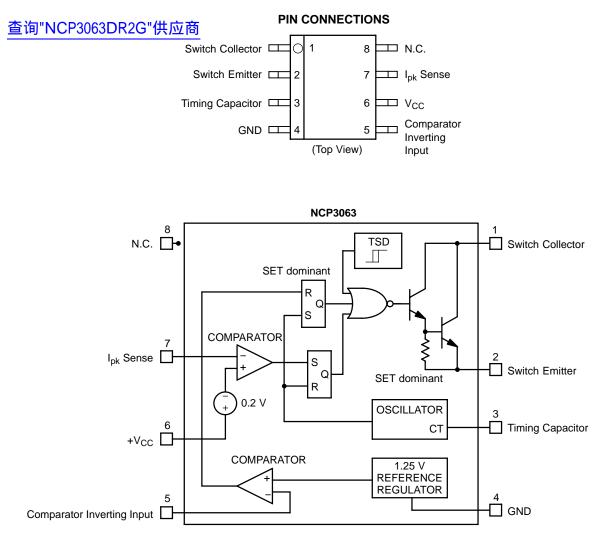


Figure 2. Block Diagram

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Pin No.	Pin Name	Description
1	Switch Collector	Internal Darlington switch collector
2	Switch Emitter	Internal Darlington switch emitter
3	Timing Capacitor	Timing Capacitor to control the switching frequency
4	GND	Ground pin for all internal circuits
5	Comparator Inverting Input	Inverting input pin of internal comparator
6	V <sub>CC</sub>	Voltage supply
7	I <sub>pk</sub> Sense	Peak Current Sense Input to monitor the voltage drop across an external resistor to limit the peak current through the circuit
8	N.C.	Pin not connected

#### MAXIMUM RATINGS (measured vs. pin 4, unless otherwise noted)

Rating	Symbol	Value	Unit
V <sub>CC</sub> pin 6	V <sub>CC</sub>	0 to +40	V
Comparator Inverting Input pin 5	V <sub>CII</sub>	– 0.2 to + V <sub>CC</sub>	V
Darlington Switch Collector pin 1	V <sub>SWC</sub>	0 to +40	V
Darlington Switch Emitter pin 2 (transistor OFF)	V <sub>SWE</sub>	– 0.6 to + V <sub>CC</sub>	V
Darlington Switch Collector to Emitter pin 1-2	V <sub>SWCE</sub>	0 to +40	V
Darlington Switch Current	I <sub>SW</sub>	1.5	А
I <sub>pk</sub> Sense pin 7	V <sub>IPK</sub>	– 0.2 to V <sub>CC</sub> + 0.2	V

#### **Power Dissipation and Thermal Characteristics**

PDIP-8 Thermal Resistance Junction-to-Air	R <sub>0JA</sub>	100	°C/W
	νθJA	100	
SOIC-8 Thermal Resistance Junction-to-Air	$R_{ ext{ heta}JA}$	180	°C/W
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C
Maximum Junction Temperature	T <sub>J MAX</sub>	+150	°C
Operating Junction Temperature Range (Note 3) NCP3063 NCP3063B, NCV3063	TJ	0 to +70 -40 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. This device series contains ESD protection and exceeds the following tests:

Pin 1–8: Human Body Model 2000 V per AEC Q100–002; 003 or JESD22/A114; A115 Machine Model Method 200 V

2. This device contains latch-up protection and exceeds 100 mA per JEDEC Standard JESD78.

- 3. The relation between junction temperature, ambient temperature and Total Power dissipated in IC is  $T_J = T_A + R_{\theta} \cdot P_D$
- 4. The pins which are not defined may not be loaded by external signals

#### ELECTRICAL/CHARACTERISTICS (V<sub>CC</sub> = 5.0 V, T<sub>J</sub> = T<sub>low</sub> to T<sub>high</sub> [Note 5], unless otherwise specified)

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
OSCILLATOR	1				-	
fosc	Frequency	$      (\text{VPin 5} = 0 \text{ V, CT} = 2.2 \text{ nF}, \\ \text{T}_{\text{J}} = 25^{\circ}\text{C} )      $	110	150	190	kHz
I <sub>DISCHG</sub> / I <sub>CHG</sub>	Discharge to Charge Current Ratio	(Pin 7 to V <sub>CC</sub> , T <sub>J</sub> = 25°C)	5.5	6.0	6.5	-
V <sub>IPK(Sense)</sub>	Current Limit Sense Voltage	(TJ = 25°C) (Note 6)	165	200	235	mV
OUTPUT SWI	TCH (Note 7)				-	
V <sub>SWCE</sub> (DROP)	Darlington Switch Collector to Emitter Voltage Drop	$      (I_{SW} = 1.0 \text{ A}, \text{ Pin 2 to GND}, \\ T_J = 25^\circ\text{C}) \text{ (Note 7)}  $		1.0	1.3	V
I <sub>C(OFF)</sub>	Collector Off–State Current	(V <sub>CE</sub> = 40 V)		0.01	100	μΑ
COMPARATO	R					
V <sub>TH</sub>	Threshold Voltage	$T_J = 25^{\circ}C$		1.250		V
		NCP3063	-1.5		+1.5	%

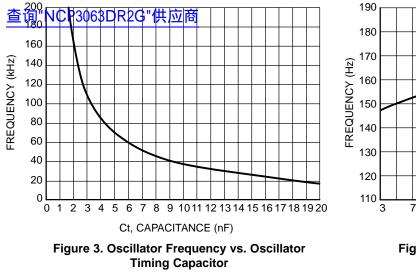
۷IH	Threshold voltage	1 j = 25 0		1.200		v
		NCP3063	-1.5		+1.5	%
		NCP3063B, NCV3063	-2		+2	%
REG <sub>LiNE</sub>	Threshold Voltage Line Regulation	$(V_{CC} = 5.0 \text{ V to } 40 \text{ V})$	-6.0	2.0	6.0	mV
I <sub>CII in</sub>	Input Bias Current	$(V_{in} = V_{th})$	-1000	-100	1000	nA

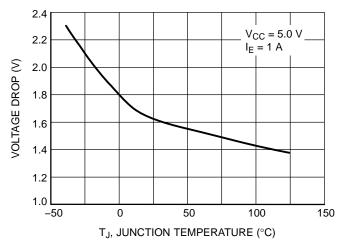
#### TOTAL DEVICE

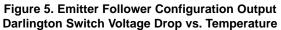
Icc	Supply Current	$\begin{array}{l} (V_{CC} = 5.0 \text{ V to } 40 \text{ V},\\ CT = 2.2 \text{ nF}, \text{ Pin } 7 = V_{CC},\\ \text{VPin } 5 > V_{th}, \text{ Pin } 2 = \text{GND},\\ \text{remaining pins open} \end{array}$		7.0	mA
Thermal Shutdown Threshold			160		°C
	Hysteresis		10		°C

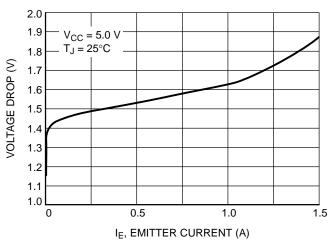
NCP3063: T<sub>low</sub> = 0°C, T<sub>high</sub> = +70°C; NCP3063B, NCV3063: T<sub>low</sub> = -40°C, T<sub>high</sub> = +125°C
 The V<sub>IPK(Sense)</sub> Current Limit Sense Voltage is specified at static conditions. In dynamic operation the sensed current turn–off value depends on comparator response time and di/dt current slope. See the Operating Description section for details.
 Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.
 NOP3063: T<sub>low</sub> = 0°C, T<sub>high</sub> = +70°C; NOP3063: T<sub>low</sub> = -40°C, T<sub>high</sub> = +125°C
 The V<sub>IPK(Sense)</sub> Current Limit Sense Voltage is specified at static conditions. In dynamic operation the sensed current turn–off value depends on comparator response time and di/dt current slope. See the Operating Description section for details.
 Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

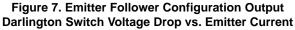
8. NCV prefix is for automotive and other applications requiring site and change control.











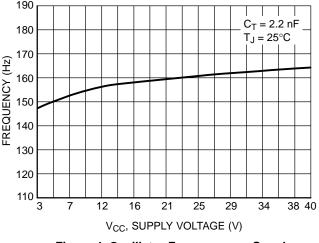


Figure 4. Oscillator Frequency vs. Supply Voltage

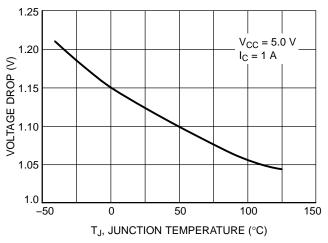


Figure 6. Common Emitter Configuration Output Darlington Switch Voltage Drop vs. Temperature

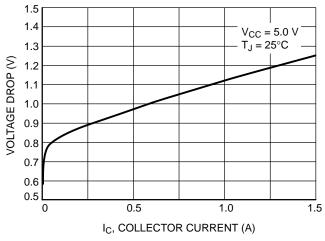


Figure 8. Common Emitter Configuration Output Darlington Switch Voltage Drop vs. Collector Current

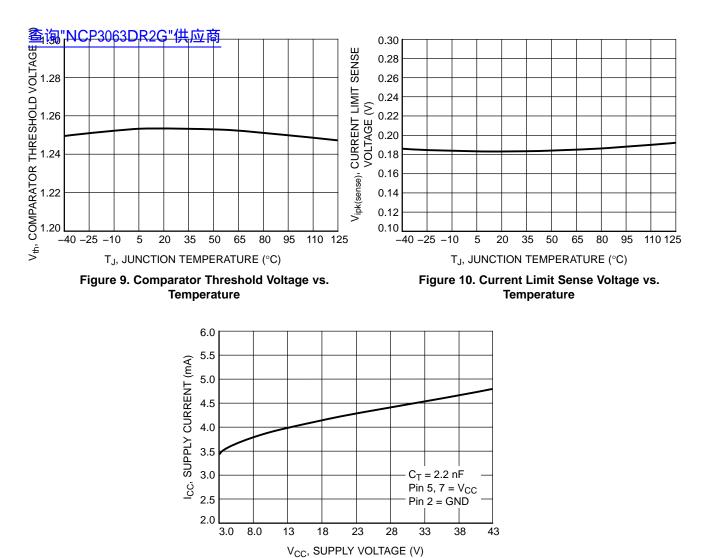


Figure 11. Standby Supply Current vs. Supply Voltage

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#### INTRODUCTION

The NCP3063 is a monolithic power switching regulator optimized for dc to dc converter applications. The combination of its features enables the system designer to directly implement step–up, step–down, and voltage– inverting converters with a minimum number of external components. Potential applications include cost sensitive consumer products as well as equipment for industrial markets. A representative block diagram is shown in Figure 2.

#### **Operating Description**

The NCP3063 is a hysteric, dc–dc converter that uses a gated oscillator to regulate output voltage. In general, this mode of operation is somewhat analogous to a capacitor charge pump and does not require dominant pole loop compensation for converter stability. The Typical Operating Waveforms are shown in Figure 12. The output voltage waveform shown is for a step–down converter with the ripple and phasing exaggerated for clarity. During initial converter startup, the feedback comparator senses that the output voltage level is below nominal. This causes the output switch to turn on and off at a frequency and duty cycle

controlled by the oscillator, thus pumping up the output filter capacitor. When the output voltage level reaches nominal, the output switch next cycle turning on is inhibited. The feedback comparator will enable the switching immediately when the load current causes the output voltage to fall below nominal. Under these conditions, output switch conduction can be enabled for a partial oscillator cycle, a partial cycle plus a complete cycle, multiple cycles, or a partial cycle plus multiple cycles. (See AN920/D for more information).

#### Oscillator

The oscillator frequency and off-time of the output switch are programmed by the value selected for timing capacitor  $C_T$ . Capacitor  $C_T$  is charged and discharged by a 1 to 6 ratio internal current source and sink, generating a positive going sawtooth waveform at Pin 3. The oscillator peak and valley voltage difference is 500 mV typically. To calculate the  $C_T$ capacitor value for required oscillator frequency, use the equations found in Figure 13. An Excel based design tool can be found at www.onsemi.com on the NCP3063 product page.

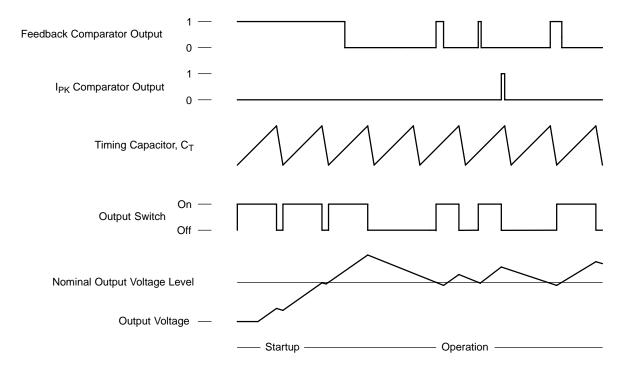
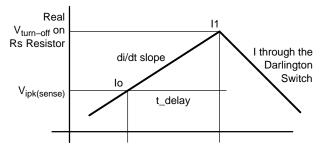


Figure 12. Typical Operating Waveforms

#### Peak Current Sense Comparator. 当道,"NCP3063DR2G"供以商

查询,"NCP3063DR2G."开以商 With a voltage ripple gated converter operating under normal conditions, output switch conduction is initiated by the Voltage Feedback comparator and terminated by the oscillator. Abnormal operating conditions occur when the converter output is overloaded or when feedback voltage sensing is lost. Under these conditions, the Ipk Current Sense comparator will protect the Darlington output Switch. The switch current is converted to a voltage by inserting a fractional ohm resistor, R<sub>SC</sub>, in series with V<sub>CC</sub> and the Darlington output switch. The voltage drop across R<sub>SC</sub> is monitored by the Current Sense comparator. If the voltage drop exceeds 200 mV with respect to V<sub>CC</sub>, the comparator will set the latch and terminate output switch conduction on a cycle-by-cycle basis. This Comparator/Latch configuration ensures that the Output Switch has only a single on-time during a given oscillator cycle.



The  $V_{IPK(Sense)}$  Current Limit Sense Voltage threshold is specified at static conditions. In dynamic operation the sensed current turn–off value depends on comparator response time and di/dt current slope.

Figures 14 through 22 show the simplicity and flexibility of the NCP3063. Three main converter topologies are demonstrated with actual test data shown below each of the circuit diagrams. Real V<sub>turn-off</sub> on Rsc resistor

 $V_{turn_off} = V_{ipk(sense)} + Rs \cdot (t_{delay} \cdot di/dt)$ 

Typical  $I_{pk}$  comparator response time t\_delay is 350 ns. The di/dt current slope is growing with voltage difference on the inductor pins and with decreasing inductor value.

It is recommended to check the real max peak current in the application at worst conditions to be sure that the max peak current will never get over the 1.5 A Darlington Switch Current max rating.

#### Thermal Shutdown

Internal thermal shutdown circuitry is provided to protect the IC in the event that the maximum junction temperature is exceeded. When activated, typically at 160°C, the Output Switch is disabled. The temperature sensing circuit is designed with 10°C hysteresis. The Switch is enabled again when the chip temperature decreases to at least 150°C threshold. **This feature is provided to prevent catastrophic failures from accidental device overheating. It is not intended to be used as a replacement for proper heatsinking.** 

#### **Output Switch**

The output switch is designed in a Darlington configuration. This allows the application designer to operate at all conditions at high switching speed and low voltage drop. The Darlington Output Switch is designed to switch a maximum of 40 V collector to emitter voltage and current up to 1.5 A.

### APPLICATIONS

Figure 13 gives the relevant design equations for the key parameters. Additionally, a complete application design aid for the NCP3063 can be found at www.onsemi.com.

查询 <sup>N</sup> NEP3063D	R2G"供应 <b>譖</b> p-Down	Step-Up	Voltage-Inverting
ton toff	Vout + VF Vin - VSWCE - Vout	$\frac{V_{out} + V_{F} - V_{in}}{V_{in} - V_{SWCE}}$	$\frac{ V_{out}  + V_{F}}{V_{in} - V_{SWCE}}$
t <sub>on</sub>	$\frac{\frac{t_{on}}{t_{off}}}{f\left(\frac{t_{on}}{t_{off}}+1\right)}$	$\frac{\frac{t_{on}}{t_{off}}}{f\left(\frac{t_{on}}{t_{off}}+1\right)}$	$\frac{\frac{t_{on}}{t_{off}}}{f\left(\frac{t_{on}}{t_{off}}+1\right)}$
CT	Ст	$T = \frac{381.6 \cdot 10^{-6}}{f_{OSC}} - 343 \cdot 10^{-12}$	
I <sub>L(avg)</sub>	lout	$I_{out}\left(\frac{t_{on}}{t_{off}}+1\right)$	$I_{out}\left(\frac{t_{On}}{t_{off}}+1\right)$
I <sub>pk (Switch)</sub>	$I_{L(avg)} + \frac{\Delta I_{L}}{2}$	$I_{L(avg)} + \frac{\Delta I_{L}}{2}$	$I_{L(avg)} + \frac{\Delta I_{L}}{2}$
R <sub>SC</sub>	0.20 Ipk (Switch)	0.20 <sup>I</sup> pk (Switch)	0.20 Ipk (Switch)
L	$\left(\frac{V_{in}-V_{SWCE}-V_{out}}{\DeltaI_L}\right)t_{on}$	$\left(\frac{V_{in}-V_{SWCE}}{\DeltaI_L}\right)t_{on}$	$\left( \frac{V_{in}-V_{SWCE}}{\DeltaI_L} \right) t_{on}$
V <sub>ripple(pp)</sub>	$\Delta I_{L} \sqrt{\left(\frac{1}{8 f C_{O}}\right)^{2} + (ESR)^{2}}$	$\approx \frac{t_{on} \ l_{out}}{C_{O}} + \Delta I_{L} \cdot ESR$	$\approx \frac{t_{OO} \ l_{OUt}}{C_O} + \Delta I_L \cdot ESR$
V <sub>out</sub>	$V_{TH}\left(\frac{R_2}{R_1} + 1\right)$	$V_{TH}\left(\frac{R_2}{R_1} + 1\right)$	$V_{TH}\left(\frac{R_2}{R_1} + 1\right)$

#### The Following Converter Characteristics Must Be Chosen:

Vin - Nominal operating input voltage.

Vout - Desired output voltage.

I<sub>out</sub> – Desired output current.

 $\Delta I_L$  – Desired peak–to–peak inductor ripple current. For maximum output current it is suggested that  $\Delta I_L$  be chosen to be less than 10% of the average inductor current  $I_{L(avg)}$ . This will help prevent  $I_{pk (Switch)}$  from reaching the current limit threshold set by R<sub>SC</sub>. If the design goal is to use a minimum inductance value, let  $\Delta I_L = 2(I_{L(avg)})$ . This will proportionally reduce converter output current capability.

*f* – Maximum output switch frequency.

 $V_{ripple(pp)}$  – Desired peak–to–peak output ripple voltage. For best performance the ripple voltage should be kept to a low value since it will directly affect line and load regulation. Capacitor C<sub>O</sub> should be a low equivalent series resistance (ESR) electrolytic designed for switching regulator applications.

9. V<sub>SWCE</sub> – Darlington Switch Collector to Emitter Voltage Drop, refer to Figures 5, 6, 7 and 8.

10. V<sub>F</sub> – Output rectifier forward voltage drop. Typical value for 1N5819 Schottky barrier rectifier is 0.4 V.

11. The calculated  $t_{on}/t_{off}$  must not exceed the minimum guaranteed oscillator charge to discharge ratio.

Figure 13. Design Equations

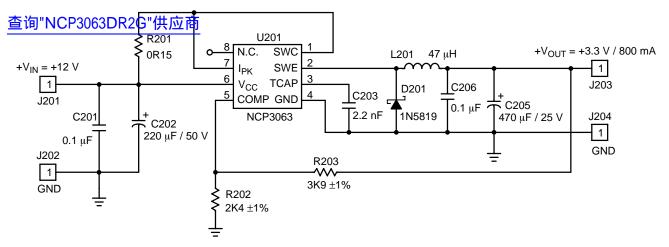


Figure 14. Typical Buck Application Schematic

#### Value of Components

Name	Value
L201	47 μH, I <sub>sat</sub> > 1.5 A
D201	1 A, 40 V Schottky Rectifier
C202	220 μF, 50 V, Low ESR
C205	470 μF, 25 V, Low ESR
C203	2.2 nF Ceramic Capacitor

Name	Value
R201	150 mΩ, 0.5 W
R202	2.40 kΩ
R203	3.90 kΩ
C201	100 nF Ceramic Capacitor
C202	100 nF Ceramic Capacitor

#### **Test Results**

Test	Condition	Results
Line Regulation	$V_{in} = 9 V \text{ to } 12 V, I_0 = 800 \text{ mA}$	8 mV
Load Regulation	$V_{in}$ = 12 V, I <sub>o</sub> = 80 mA to 800 mA	9 mV
Output Ripple	$V_{in}$ = 12 V, I <sub>o</sub> = 40 mA to 800 mA	$\leq$ 85 mV <sub>pp</sub>
Efficiency	$V_{in}$ = 12 V, I <sub>o</sub> = 400 mA to 800 mA	> 73%
Short Circuit Current	$V_{in}$ = 12 V, $R_{load}$ = 0.15 $\Omega$	1.25 A

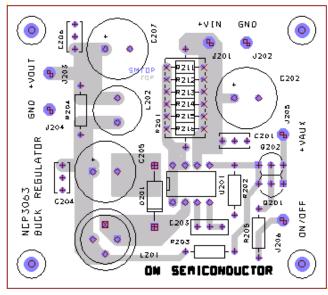
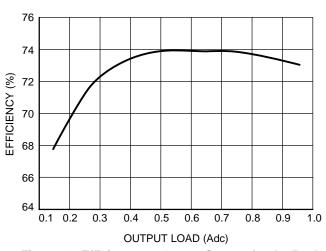
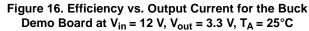


Figure 15. Buck Demoboard Layout





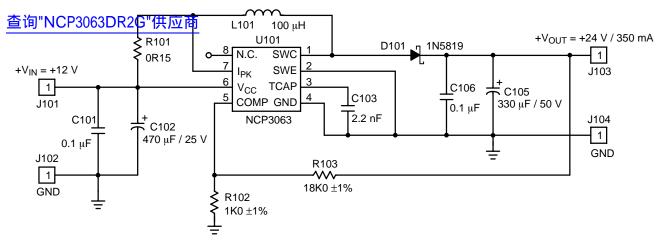


Figure 17. Typical Boost Application Schematic

#### Value of Components

Name	Value
L101	100 μH, I <sub>sat</sub> > 1.5 A
D101	1 A, 40 V Schottky Rectifier
C102	470 μF, 25 V, Low ESR
C105	330 μF, 50 V, Low ESR
C103	2.2 nF Ceramic Capacitor

Name	Value
R101	150 mΩ, 0.5 W
R102	1.00 kΩ
R103	18.00 kΩ
C101	100 nF Ceramic Capacitor
C106	100 nF Ceramic Capacitor

#### **Test Results**

Test	Condition	Results
Line Regulation	$V_{in} = 9 V$ to 15 V, $I_0 = 250 mA$	2 mV
Load Regulation	$V_{in}$ = 12 V, I <sub>o</sub> = 30 mA to 350 mA	5 mV
Output Ripple	$V_{in}$ = 12 V, I <sub>o</sub> = 10 mA to 350 mA	$\leq$ 350 mV <sub>pp</sub>
Efficiency	$V_{in}$ = 12 V, I <sub>o</sub> = 50 mA to 350 mA	> 85.5%

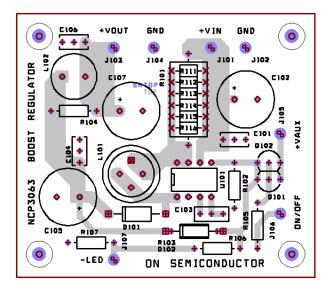
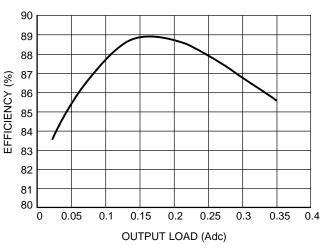
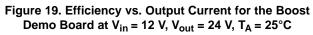


Figure 18. Boost Demoboard Layout





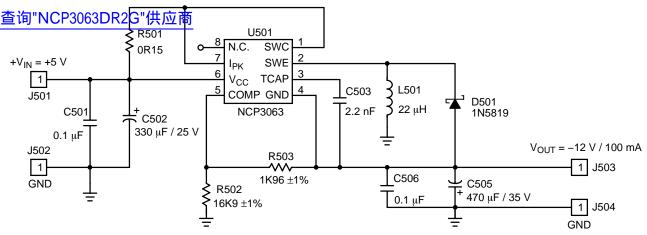


Figure 20. Typical Voltage Inverting Application Schematic

#### Value of Components

Name	Value
L501	22 μH, I <sub>sat</sub> > 1.5 A
D501	1 A, 40 V Schottky Rectifier
C502	330 μF, 25 V, Low ESR
C505	470 μF, 35 V, Low ESR
C503	2.2 nF Ceramic Capacitor

Name	Value
R501	150 mΩ, 0.5 W
R502	16.9 kΩ
R503	1.96 kΩ
C501	100 nF Ceramic Capacitor
C506	100 nF Ceramic Capacitor

#### **Test Results**

Test	Condition	Results
Line Regulation	$V_{in}$ = 4.5 V to 6 V, I <sub>o</sub> = 50 mA	1.5 mV
Load Regulation	$V_{in} = 5 \text{ V}, I_0 = 10 \text{ mA to } 100 \text{ mA}$	1.6 mV
Output Ripple	$V_{in} = 5 \text{ V}, I_0 = 0 \text{ mA to } 100 \text{ mA}$	$\leq$ 300 mV <sub>pp</sub>
Efficiency	V <sub>in</sub> = 5 V, I <sub>o</sub> = 100 mA	49.8%
Short Circuit Current	$V_{in} = 5 \text{ V}, \text{ R}_{load} = 0.15 \Omega$	0.885 A

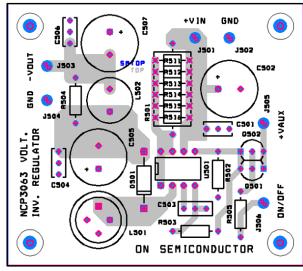
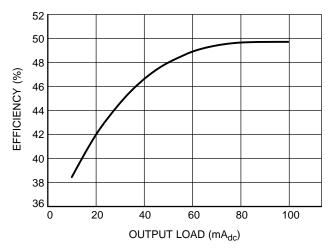
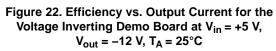


Figure 21. Voltage Inverting Demoboard Layout





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Device	Package	Shipping <sup>†</sup>	
NCP3063PG	PDIP-8 (Pb-Free)	50 Units / Rail	
NCP3063BPG	PDIP-8 (Pb-Free)	50 Units / Rail	
NCP3063DR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
NCP3063BDR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
NCP3063	DFN-8 (Pb-Free)	TBD	
NCV3063PG	PDIP-8 (Pb-Free)	50 Units / Rail	
NCV3063DR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	

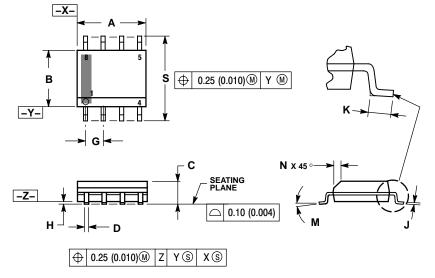
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NCV prefix is for automotive and other applications requiring site and change control.

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#### PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 **ISSUE AH** 

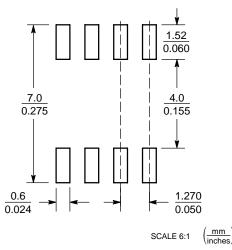


NOTES:

- VOTES:
  DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 (2020)
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 4.
- PER SIDE. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT 5.
- MAXIMUM MATERIAL CONDITION. 6. 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

	MILLIMETERS		MILLIMETERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27 BSC		0.050 BSC		
н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
ĸ	0.40	1.27	0.016	0.050	
Μ	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***

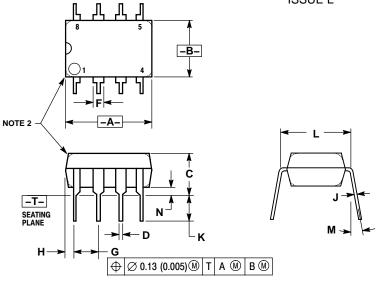


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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### PACKAGE DIMENSIONS

**8 LEAD PDIP** CASE 626-05 ISSUE L



- NOTES: 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL. 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS). 3. DIMENSIONING AND TOLERANCING PER ANSI 1414 544 1982

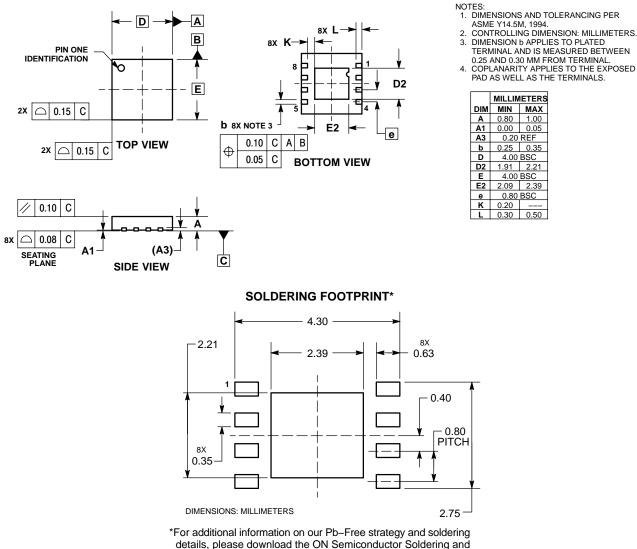
Y14.5M, 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
C	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54	BSC	0.100	BSC
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
Κ	2.92	3.43	0.115	0.135
L	7.62	BSC	0.300 BSC	
Μ		10°		10°
Ν	0.76	1.01	0.030	0.040
Style Pin	1: 1. AC IN 2. DC + 3. DC - 4. AC IN 5. GROU	IN IN		

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#### PACKAGE DIMENSIONS

8 PIN DFN, 4x4 CASE 488AF-01 **ISSUE B** 



Mounting Techniques Reference Manual, SOLDERRM/D.

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